



# TGA2760-SM

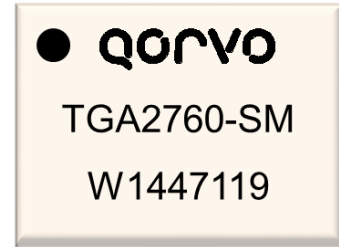
## 10 – 11.7 GHz Power Amplifier

### Product Overview

Qorvo's TGA2760-SM is a packaged X-band high power amplifier utilizing Qorvo's production GaAs pHEMT and GaN processes. The TGA2760-SM operates from 10 – 11.7 GHz and typically provides 16W saturated power with power-added efficiency of 36% and large signal gain 30 dB. Third-order intermodulation is better than -30 dBc at 3 dB backed off from Psat. Along with the higher performance, an additional feature is an integrated power detector allowing the user to accurately monitor the output power of the unit.

The TGA2760-SM is packaged in a small air-cavity surface mount package and matched to 50 ohms with integrated DC blocking capacitors on both RF I/O ports simplifying system integration.

Lead-free and RoHS compliant.



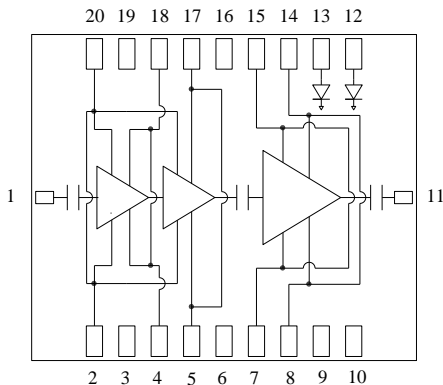
20-Lead 8.0 x 10.0 x 2 mm Package

### Key Features

- Frequency Range: 10 – 11.7 GHz
- Power: +42 dBm Psat
- Gain: 33 dB
- Integrated Power Detector
- Bias:  $V_{D1} = V_{D2} = +7\text{ V}$ ,  $I_{D1} + I_{D2} = 1000\text{ mA}$ ,  $V_{D3} = +28\text{ V}$ ,  $I_{D3} = 260\text{ mA}$
- Package Dimensions: 8.0 x 10.0 x 2 mm

*Performance is typical across frequency. Please reference electrical specification table and data plots for more details*

### Functional Block Diagram



Top View

### Applications

- Point-to-Point Radio

### Ordering Information

| Part No.       | Description                        |
|----------------|------------------------------------|
| TGA2760-SM     | 10 – 11.7 GHz Power Amplifier      |
| TGA2760-SM-T/R | 500 pieces on a 7" reel (standard) |
| TGA2760-SM EVB | Evaluation Board                   |

## Absolute Maximum Ratings

| Parameter                                    | Rating        |
|--|---------------|
| Drain Voltage, $V_{D1}, V_{D2}$              | +9 V          |
| Drain Voltage, $V_{D3}$                      | +32 V         |
| Drain Current, $I_{D1} + I_{D2}$             | 3850 mA       |
| Drain Current, $I_{D3}$                      | 2000 mA       |
| Power Dissipation, Driver Stages, $P_{DISS}$ | 14.8 W        |
| Power Dissipation, Final Stage, $P_{DISS}$   | 28.8 W        |
| RF Input Power, CW, 50 $\Omega$ , T = 25 °C  | +29 dBm       |
| Mounting Temperature (30 Seconds)            | 260 °C        |
| Storage Temperature                          | -40 to 150 °C |

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

## Recommended Operating Conditions

| Parameter                                    | Min | Typ  | Max | Units |
|--|-----|------|-----|-------|
| Operating Temp. Range                        | -40 | +25  | +85 | °C    |
| $V_{D1}, V_{D2}$                             |     | +7   |     | V     |
| $V_{D3}$                                     |     | +28  |     | V     |
| $I_{D1} + I_{D2}$                            |     | 1000 |     | mA    |
| $I_{D3}$                                     |     | 260  |     | mA    |
| $V_{G12}$                                    |     | -0.7 |     | V     |
| $V_{G3}$                                     |     | -2.6 |     | V     |
| $I_{D1} + I_{D2}$ drive<br>(at +39 dBm Pout) |     | 1018 |     | mA    |
| $I_{D3}$ drive<br>(at +39 dBm Pout)          |     | 930  |     | mA    |

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

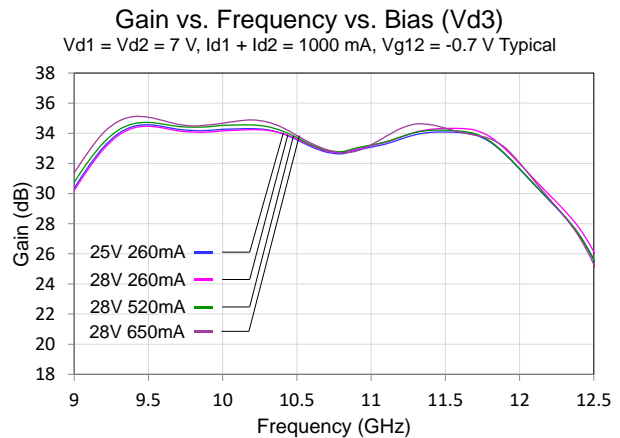
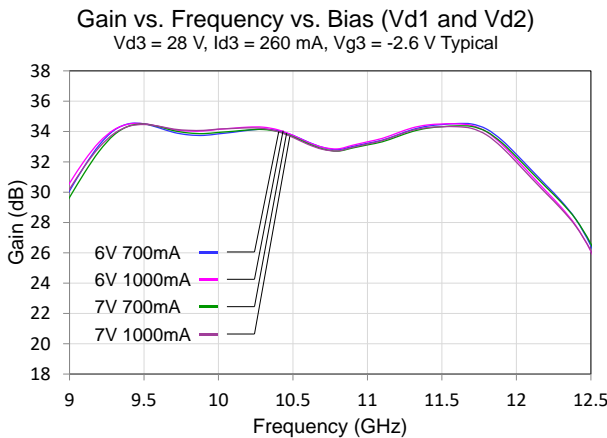
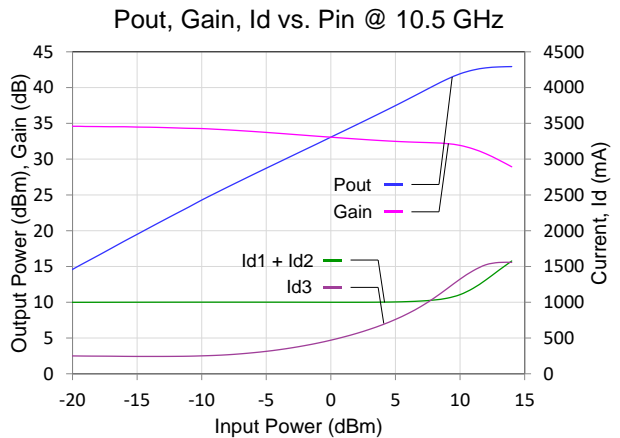
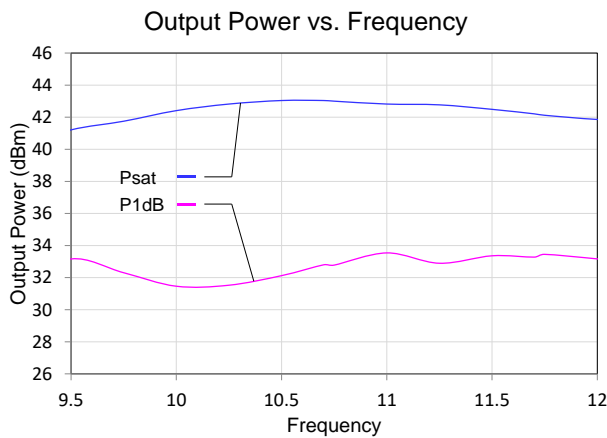
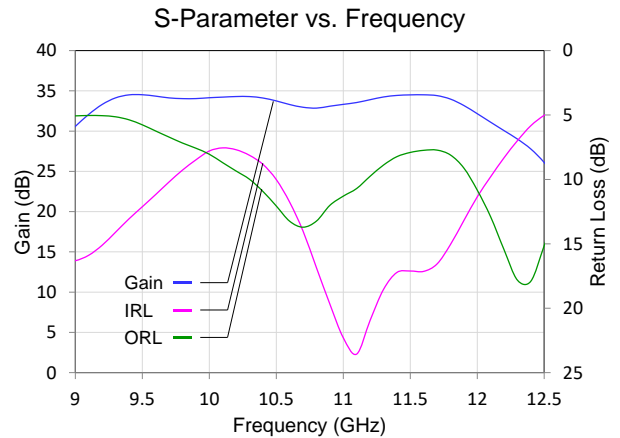
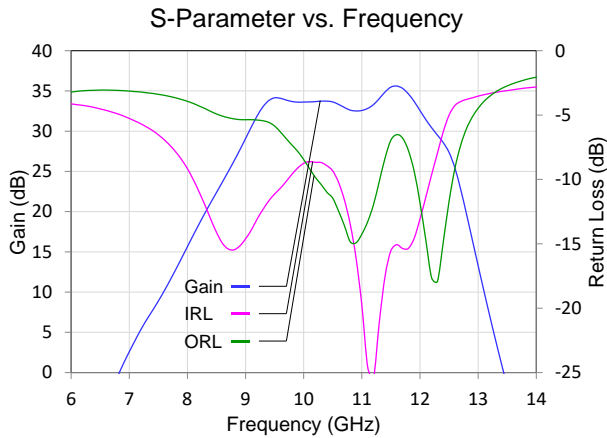
## Electrical Specifications

| Parameter                                       | Conditions <sup>(1)</sup> | Min   | Typ   | Max  | Units    |
|---|---------------------------|-------|-------|------|----------|
| RF Frequency Range                              |                           | 10    |       | 11.7 | GHz      |
| Small Signal Gain                               |                           | 27    | 33    |      | dB       |
| Input Return Loss, IRL                          |                           |       | 8     |      | dB       |
| Output Return Loss, ORL                         |                           |       | 8     |      | dB       |
| Output Power at Pin = +12 dBm                   |                           | +39.5 | +42   |      | dBm      |
| Power Added Efficiency                          |                           |       | 36    |      | %        |
| Output Third Order Intercept, TOI @ 30 dBm/Tone |                           |       | +52   |      | dBm      |
| Gain Temperature Coefficient                    |                           |       | -0.05 |      | dB / °C  |
| Power Temperature Coefficient                   |                           |       | -0.01 |      | dBm / °C |

Notes:  
1. Test conditions unless otherwise noted:  $V_{D1} = V_{D2} = +7$  V,  $I_{D1} + I_{D2} = 1000$  mA,  $V_{G1} = V_{G2} = -0.7$  V,  $V_{D3} = +28$  V,  $I_{D3} = 260$  mA,  $V_{G3} = -2.6$  V, Temp = +25 °C,  $Z_0 = 50$   $\Omega$

Performance Plots

Test conditions unless otherwise noted:  $V_{D1} = V_{D2} = +7\text{ V}$ ,  $I_{D1} + I_{D2} = 1000\text{ mA}$ ,  $V_{G1} = V_{G2} = -0.7\text{ V}$ ,  $V_{D3} = +28\text{ V}$ ,  $I_{D3} = 260\text{ mA}$ ,  $V_{G3} = -2.6\text{ V}$ ,  $\text{Temp} = +25\text{ }^\circ\text{C}$ ,  $Z_0 = 50\text{ }\Omega$

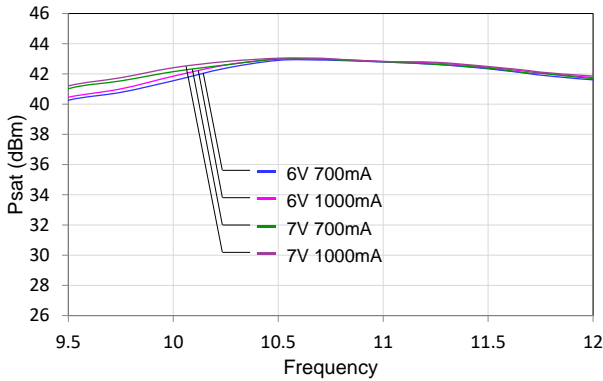


**Performance Plots**

Test conditions unless otherwise noted:  $V_{D1} = V_{D2} = +7\text{ V}$ ,  $I_{D1} + I_{D2} = 1000\text{ mA}$ ,  $V_{G1} = V_{G2} = -0.7\text{ V}$ ,  $V_{D3} = +28\text{ V}$ ,  $I_{D3} = 260\text{ mA}$ ,  $V_{G3} = -2.6\text{ V}$ ,  $\text{Temp} = +25\text{ }^\circ\text{C}$ ,  $Z_0 = 50\text{ }\Omega$

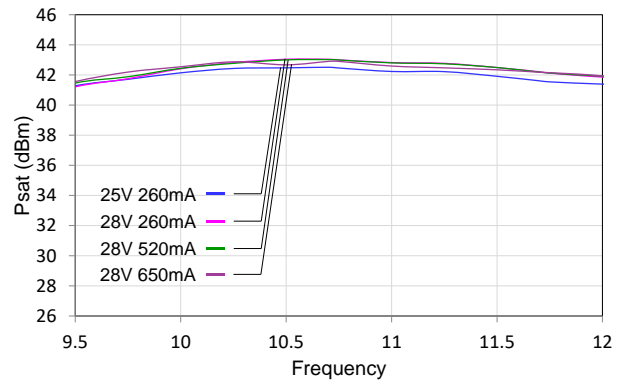
**Psat vs. Frequency vs. Bias (Vd1 and Vd2)**

$V_{d3} = 28\text{ V}$ ,  $I_{d3} = 260\text{ mA}$ ,  $V_{g3} = -2.6\text{ V}$  Typical



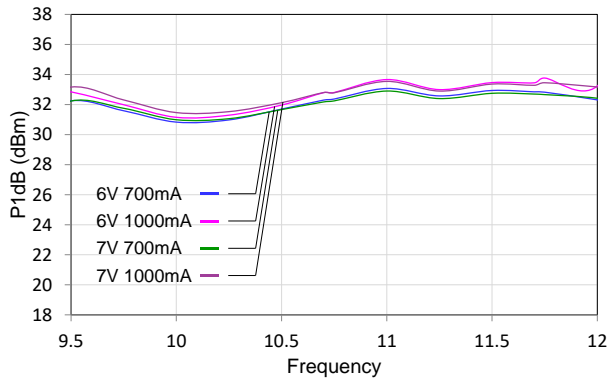
**Psat vs. Frequency vs. Bias (Vd3)**

$V_{d1} = V_{d2} = 7\text{ V}$ ,  $I_{d1} + I_{d2} = 1000\text{ mA}$ ,  $V_{g12} = -0.7\text{ V}$  Typical



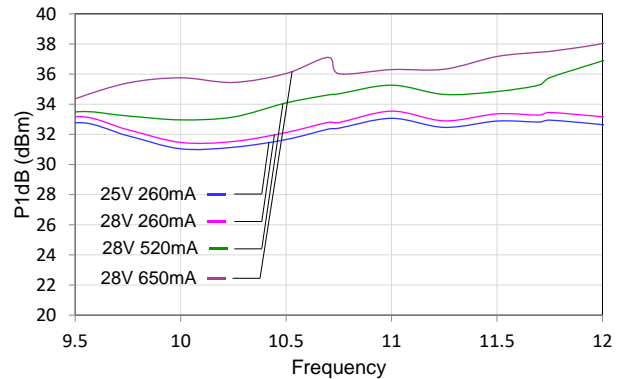
**P1dB vs. Frequency vs. Bias (Vd1 and Vd2)**

$V_{d3} = 28\text{ V}$ ,  $I_{d3} = 260\text{ mA}$ ,  $V_{g3} = -2.6\text{ V}$  Typical

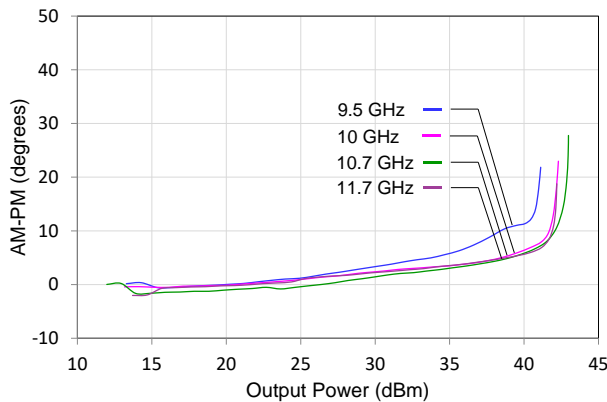


**P1dB vs. Frequency vs. Bias (Vd3)**

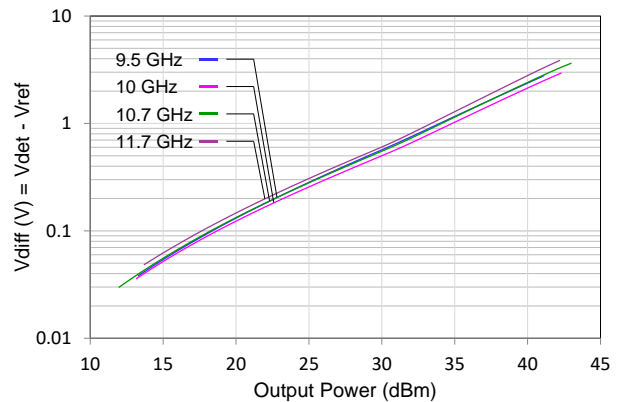
$V_{d1} = V_{d2} = 7\text{ V}$ ,  $I_{d1} + I_{d2} = 1000\text{ mA}$ ,  $V_{g12} = -0.7\text{ V}$  Typical



**AM-PM vs. Pout vs. Frequency**



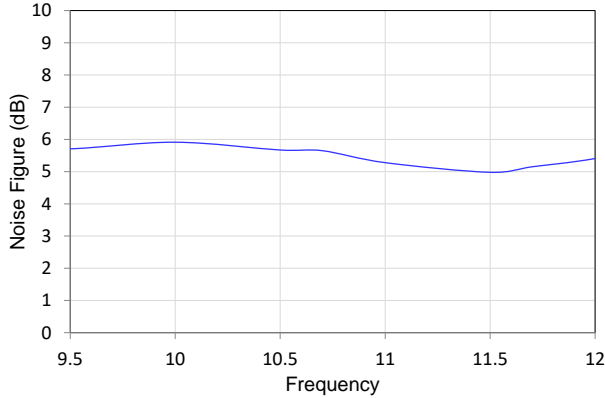
**Power Detector vs. Pout vs. Frequency**



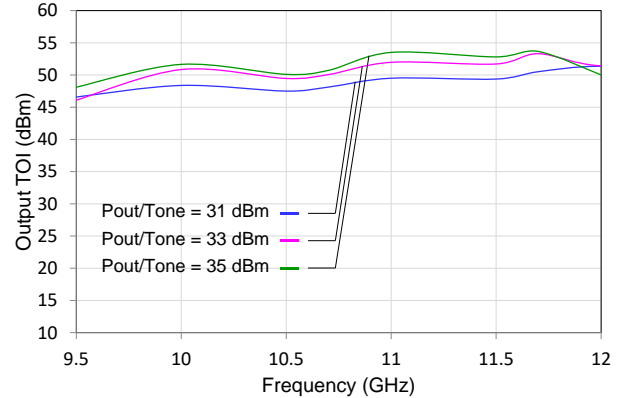
### Performance Plots

Test conditions unless otherwise noted:  $V_{D1} = V_{D2} = +7\text{ V}$ ,  $I_{D1} + I_{D2} = 1000\text{ mA}$ ,  $V_{G1} = V_{G2} = -0.7\text{ V}$ ,  $V_{D3} = +28\text{ V}$ ,  $I_{D3} = 260\text{ mA}$ ,  $V_{G3} = -2.6\text{ V}$ ,  $\text{Temp} = +25\text{ }^{\circ}\text{C}$ ,  $Z_0 = 50\text{ }\Omega$

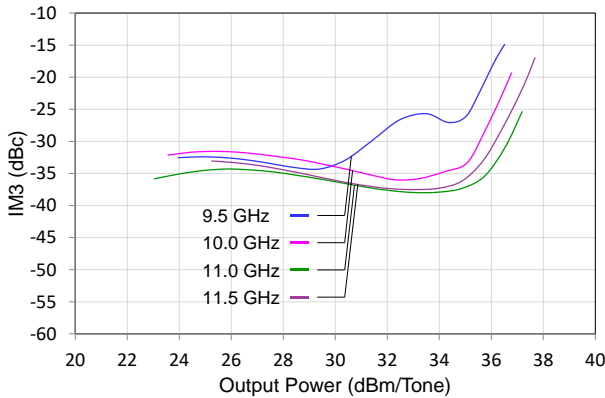
Noise Figure vs. Frequency



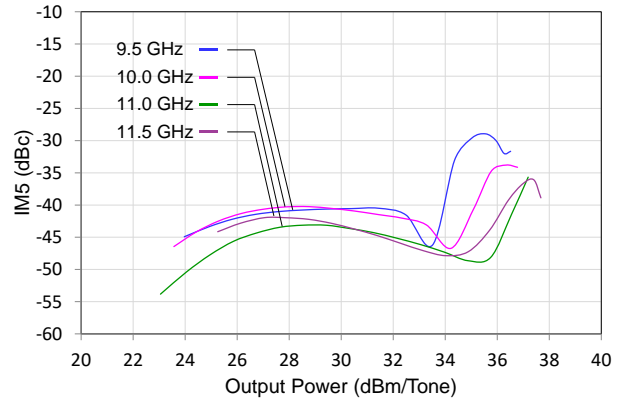
TOI vs. Frequency vs. Pout/Tone



IM3 vs. Pout/Tone vs. Frequency

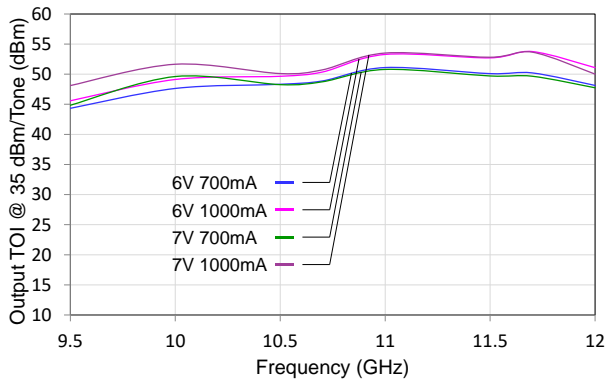


IM5 vs. Pout/Tone vs. Frequency



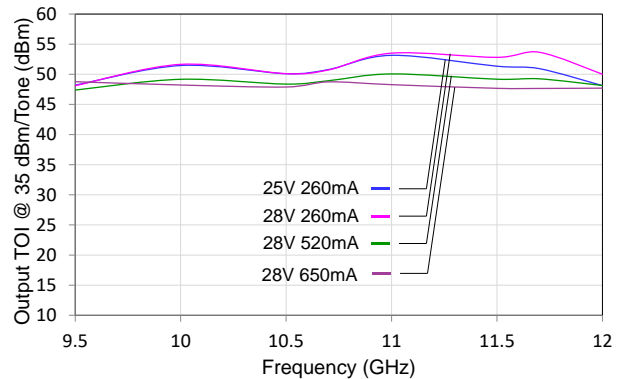
TOI vs. Frequency vs. Bias (Vd1 and Vd2)

$V_{D3} = 28\text{ V}$ ,  $I_{D3} = 260\text{ mA}$ ,  $V_{G3} = -2.6\text{ V}$  Typical



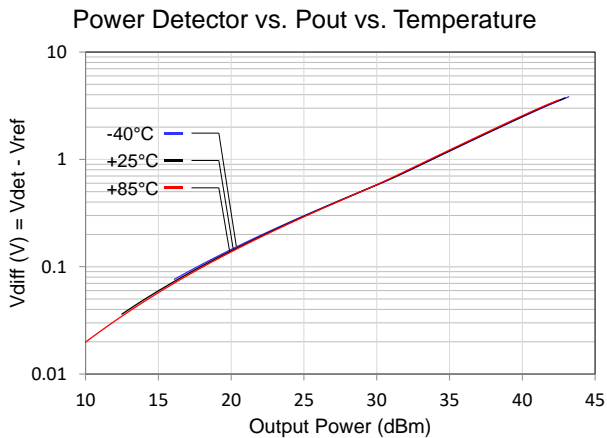
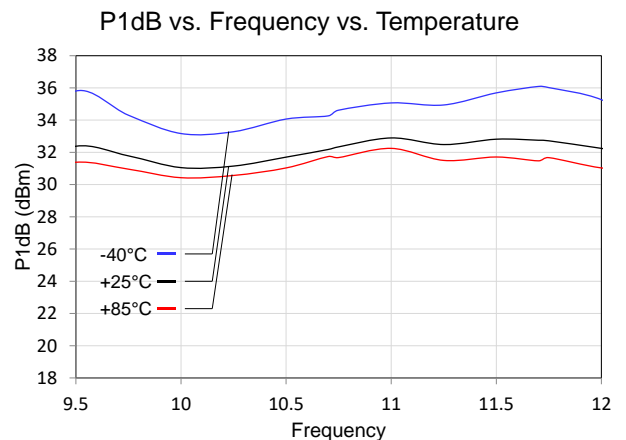
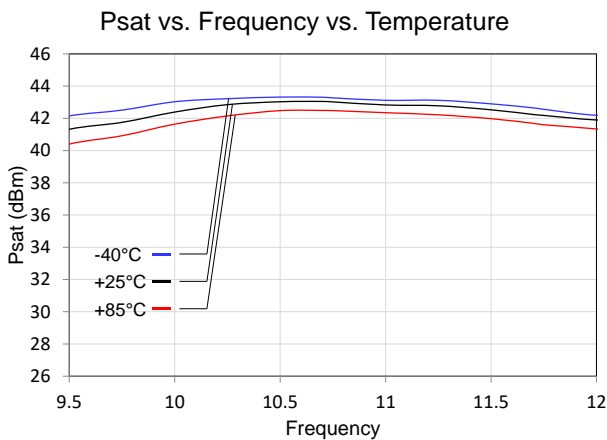
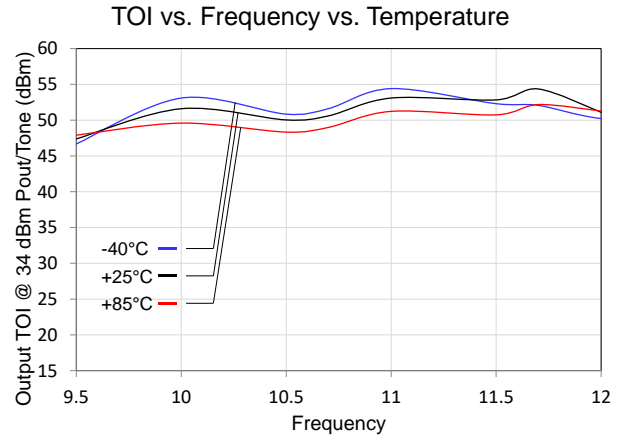
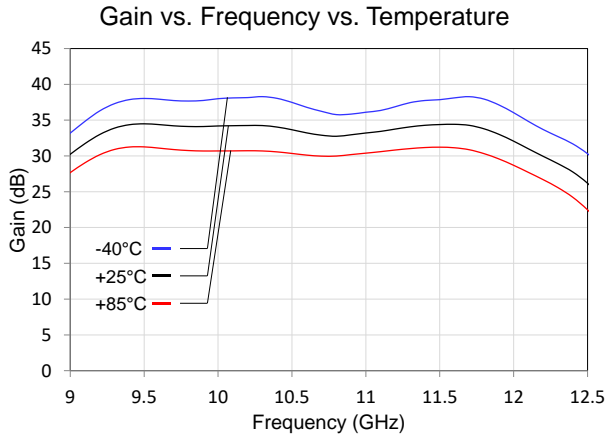
TOI vs. Frequency vs. Bias (Vd3)

$V_{D1} = V_{D2} = 7\text{ V}$ ,  $I_{D1} + I_{D2} = 1000\text{ mA}$ ,  $V_{G12} = -0.7\text{ V}$  Typical



## Performance Plots

Test conditions unless otherwise noted:  $V_{D1} = V_{D2} = +7\text{ V}$ ,  $I_{D1} + I_{D2} = 1000\text{ mA}$ ,  $V_{G1} = V_{G2} = -0.7\text{ V}$ ,  $V_{D3} = +28\text{ V}$ ,  $I_{D3} = 260\text{ mA}$ ,  $V_{G3} = -2.6\text{ V}$ ,  $\text{Temp} = +25\text{ }^\circ\text{C}$ ,  $Z_0 = 50\text{ }\Omega$



### Thermal and Reliability Information (GaAs Driver Stage)

| Parameter   | Test Conditions   | Value             | Units |
|---|---|-------------------|-------|
| Thermal Resistance ( $\theta_{JC}$ ) <sup>(1)</sup> | CW  | 8.14              | °C/W  |
| Channel Temperature, $T_{CH}$                       | $T_{base} = +85\text{ °C}$ , $V_{D\ Driver} = +7\text{ V}$ , $I_{D\ Driver} = 1000\text{ mA}$ ,<br>$P_{DISS} = 7.0\text{ W}$                              | 142               | °C    |
| Median Lifetime ( $T_M$ )                           |   | $2.0 \times 10^6$ | Hrs   |
| Thermal Resistance ( $\theta_{JC}$ ) <sup>(1)</sup> | CW  | 8.17              | °C/W  |
| Channel Temperature, $T_{CH}$ (Under RF)            | $T_{base} = +85\text{ °C}$ , $V_{D\ Driver} = +7\text{ V}$ , $I_{D\ Driver} = 1018\text{ mA}$ ,<br>$P_{OUT} = +39\text{ dBm}$ , $P_{DISS} = 7.1\text{ W}$ | 143               | °C    |
| Median Lifetime ( $T_M$ )                           |   | $1.8 \times 10^6$ | Hrs   |

Notes:

1. Thermal resistance measured at back of package.

### Thermal and Reliability Information (GaN Final Stage)

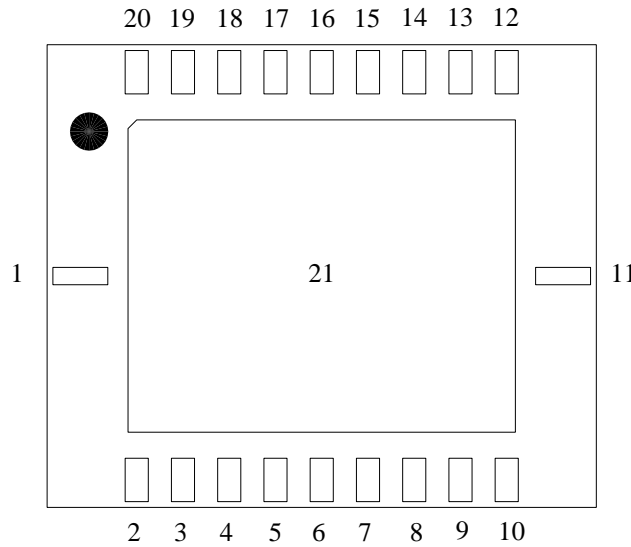
| Parameter   | Test Conditions   | Value | Units |
|---|---|-------|-------|
| Thermal Resistance ( $\theta_{JC}$ ) <sup>1</sup>     | CW  | 3.42  | °C/W  |
| Channel Temperature, $T_{CH}$ <sup>2</sup>            | $T_{base} = +85\text{ °C}$ , $V_{D\ Driver} = +28\text{ V}$ , $I_{D\ Final} = 260\text{ mA}$ ,<br>$P_{DISS} = 7.3\text{ W}$                             | 110   | °C    |
| Thermal Resistance ( $\theta_{JC}$ ) <sup>1</sup>     | CW  | 3.44  | °C/W  |
| Channel Temperature, $T_{CH}$ (Under RF) <sup>2</sup> | $T_{base} = +85\text{ °C}$ , $V_{D\ Driver} = +28\text{ V}$ , $I_{D\ Final} = 930\text{ mA}$ ,<br>$P_{OUT} = +39\text{ dBm}$ , $P_{DISS} = 18\text{ W}$ | 147   | °C    |

Notes:

1. Thermal resistance measured at back of package.
2. IR scan equivalent. Refer to the following document: [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)



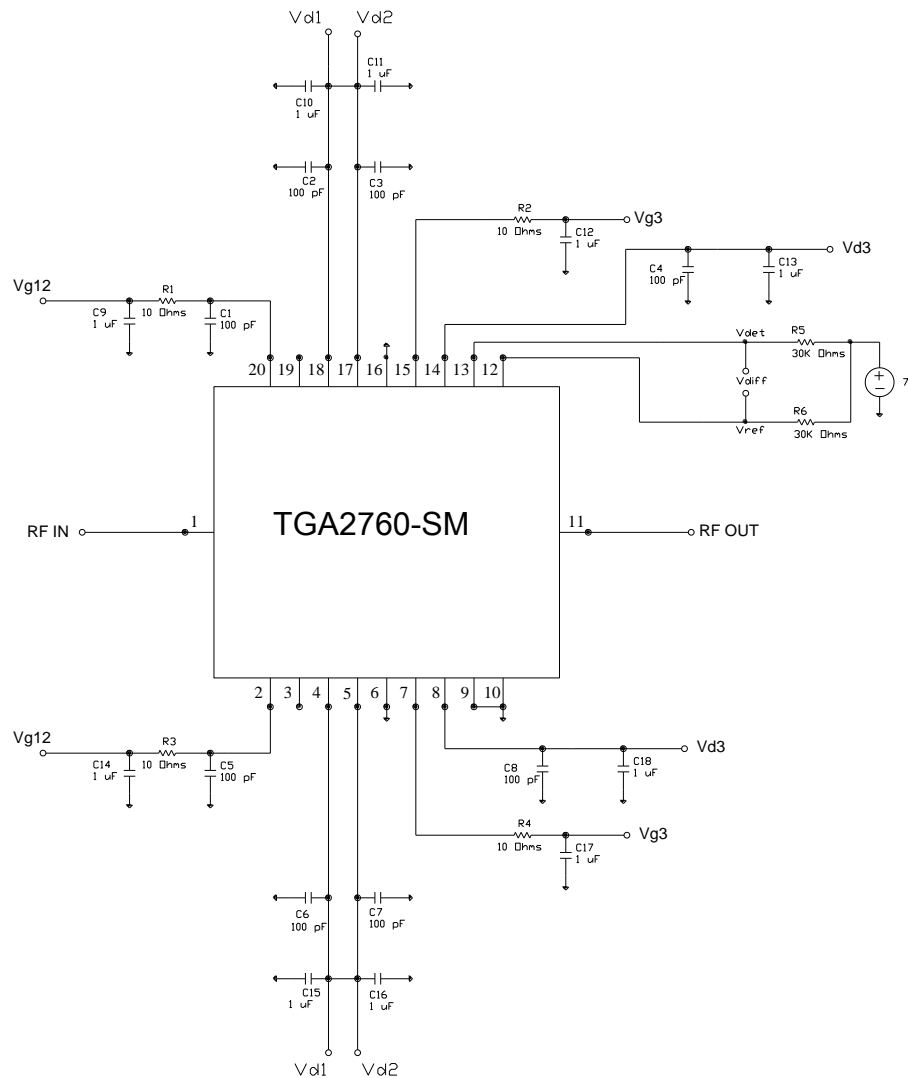
## Pin Configuration and Description



Top View

| Pad No.             | Label     | Description   |
|---------------------|-----------|---|
| 1                   | RF IN     | RF Input, matched to 50 $\Omega$ , AC Coupled.  |
| 2, 20               | $V_{G12}$ | Gate voltage. Bias network is required; can be biased from either pin, and non-biased pin can be left open; see Application Circuit on page 10 as an example.   |
| 3, 6, 9, 10, 16, 19 | NC        | No internal connection; can be grounded on PCB.   |
| 4, 18               | $V_{D1}$  | Drain voltage. Bias network is required; see Application Circuit on page 10 as an example.  |
| 5, 17               | $V_{D2}$  | Drain voltage. Bias network is required; see Application Circuit on page 10 as an example.  |
| 7, 15               | $V_{G3}$  | Gate voltage. Bias network is required; can be biased from either pin, and non-biased pin can be left opened; see Application Circuit on page 10 as an example. |
| 8, 14               | $V_{D3}$  | Drain voltage. Bias network is required; see Application Circuit on page 10 as an example.  |
| 11                  | RF OUT    | RF Output, matched to 50 ohms, AC Coupled.  |
| 12                  | $V_{REF}$ | Reference diode output voltage.   |
| 13                  | $V_{DET}$ | Detector diode output voltage. Varies with RF output power.   |
| 21                  | GND       | Backside Paddle. Multiple vias should be employed to minimize inductance and thermal resistance; see Mounting Configuration on page 13 for suggested footprint. |

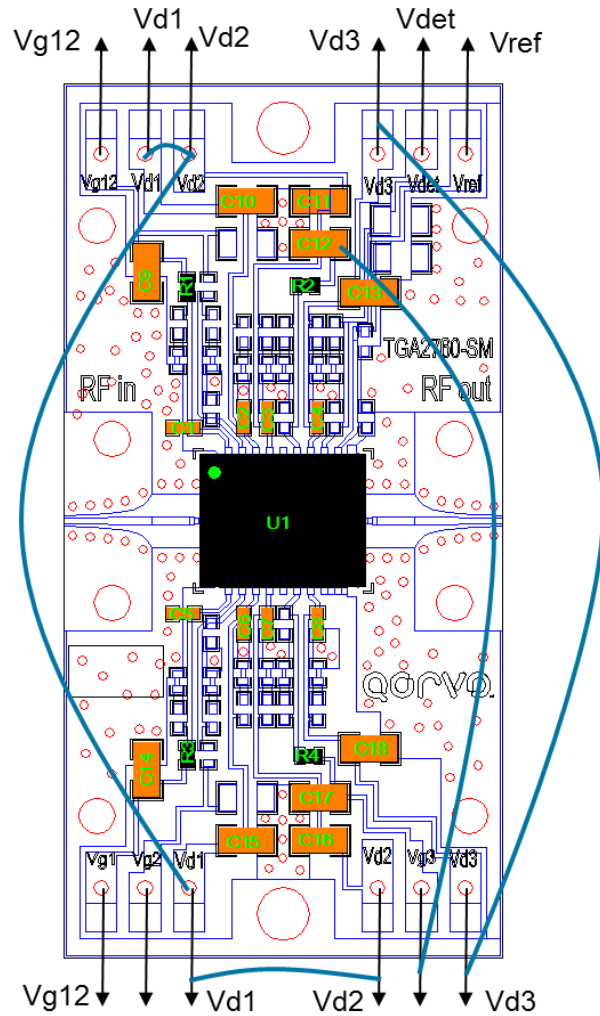
**Application Circuit**



$V_{G12}$  can be biased from either side, and the non-biased side can be left open.  
 $V_{D1}$ ,  $V_{D2}$ ,  $V_{D3}$ , must be biased from both sides.

| Bias-up Procedure   | Bias-down Procedure   |
|---|---|
| $V_{G12}$ set to $-1.5\text{ V}$  | Turn off RF signal  |
| $V_{G3}$ set to $-3.5\text{ V}$   | Reduce $V_{G12}$ to $-1.5\text{ V}$ . Ensure $I_D \sim 0\text{ mA}$ |
| $V_{D1}$ , $V_{D2}$ set to $+7\text{ V}$  | Reduce $V_{G3}$ to $-3.5\text{ V}$ . Ensure $I_D \sim 0\text{ mA}$  |
| $V_{D3}$ sets to $+28\text{ V}$   | Turn $V_{D1}$ , $V_{D2}$ , $V_{D3}$ to $0\text{ V}$                 |
| Adjust $V_{G12}$ more positive until quiescent $I_D$ is $1000\text{ mA}$ .<br>This will be $\sim V_G = -0.7\text{ V}$ typical | Turn $V_{G12}$ , $V_{G3}$ to $0\text{ V}$                           |
| Adjust $V_{G3}$ more positive until quiescent $I_D$ is $260\text{ mA}$ .<br>This will be $\sim V_G = -2.6\text{ V}$ typical   |   |
| Apply RF signal   |   |

## Application Evaluation Board



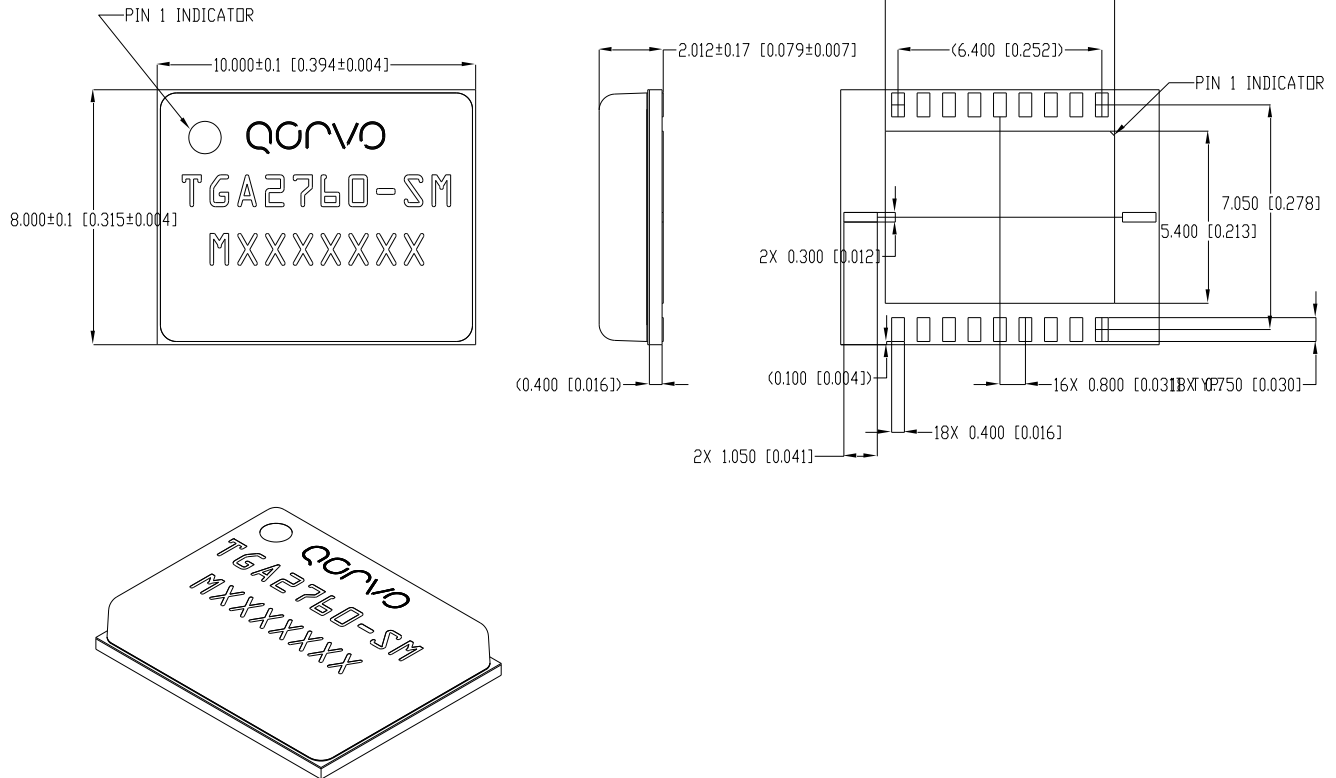
1. Board Material is RO4003 0.008" thickness with ½ oz. copper cladding

## Bill of Material

| Reference Des. | Value  | Description                  | Manuf.  | Part Number |
|----------------|--------|------------------------------|---------|-------------|
| n/a            | n/a    | Printed Circuit Board        | Qorvo   |             |
| C1 – C8        | 100 pF | Cap, 0402, +50 V, 5%, COG    | various |             |
| C9 – C18       | 1 µF   | Cap, 0603, +50 V, 5%, X5R    | various |             |
| R1 – R4        | 10 Ω   | Res, 0402, 1/16W, 5%, SMD    | various |             |
| U1             |        | 9.5 – 12 GHz Power Amplifier | Qorvo   | TGA2760-SM  |

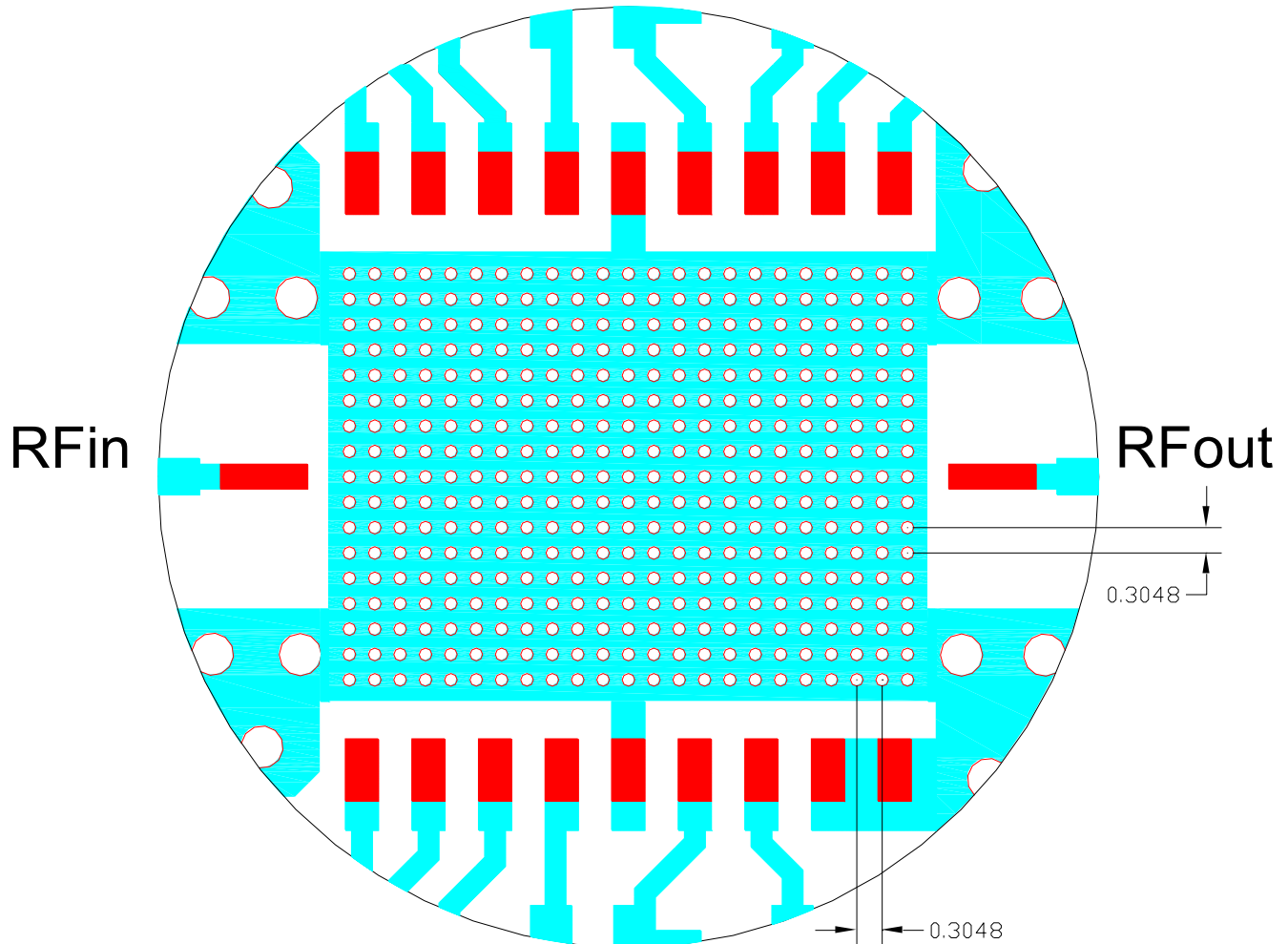
## Package Marking and Dimensions

Marking: Part Number – TGA2760-SM  
 Lot Code – MXXXXXXX



- Notes:
1. All dimensions are in millimeters. Angles are in degrees.
  2. This package is lead-free/RoHS-compliant with an embedded heat spreader, and the plating material on the leads is NiAu. It is compatible with both lead-free (maximum 260 °C reflow temperature) and tin-lead (maximum 245 °C reflow temperature) soldering processes.

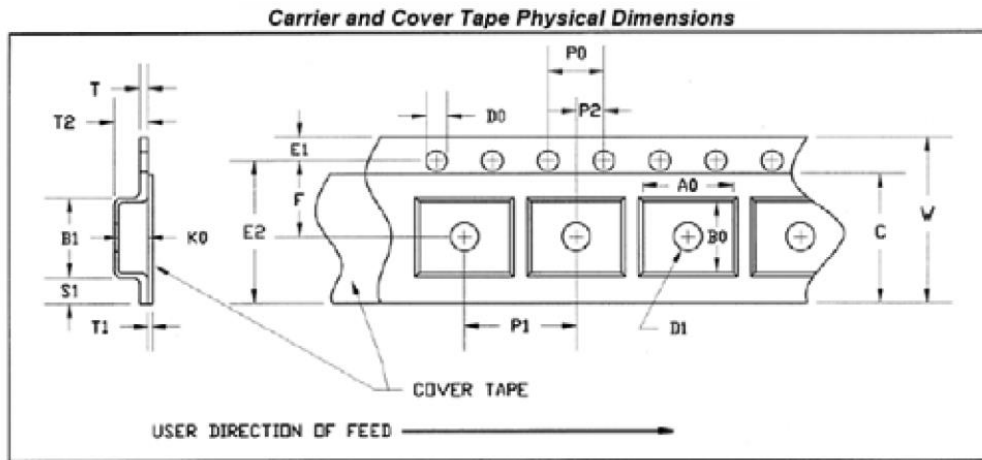
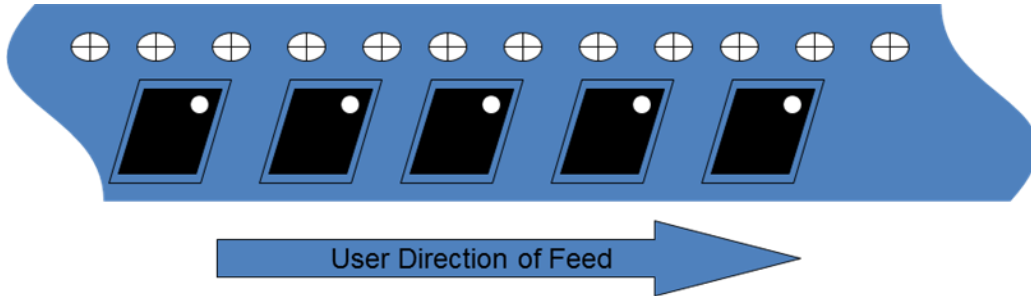
PCB Mounting Pattern



Notes:

1. The pad pattern shown has been developed and tested for optimized assembly at Qorvo. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.
2. Ground vias are critical for the proper performance of this device. Vias should have a final plated thru diameter of .1524 mm (.006").
3. For best thermal performance, vias under the ground paddle should be copper filled.

Tape and Reel Information



| Feature             | Measure                                  | Symbol | Size (in) | Size (mm) |
|---------------------|--|--------|-----------|-----------|
| Cavity              | Length                                   | A0     | 0.331     | 8.4       |
|                     | Width                                    | B0     | 0.409     | 10.4      |
|                     | Depth                                    | K0     | 0.094     | 2.4       |
|                     | Pitch                                    | P1     | 0.472     | 12.0      |
| Centerline Distance | Cavity to Perforation - Length Direction | P2     | 0.331     | 8.4       |
|                     | Cavity to Perforation - Width Direction  | F      | 0.409     | 10.4      |
| Cover Tape          | Width                                    | C      | 0.472     | 12.0      |
| Carrier Tape        | Width                                    | W      | 0.945     | 24.0      |

## Handling Precautions

| Parameter                        | Rating    | Standard                 |
|----------------------------------|-----------|--------------------------|
| ESD – Human Body Model (HBM)     | Class 1A  | ESDA / JEDEC JESD22-A114 |
| ESD – Charged Device Model (CDM) | Class C2a | JEDEC JS-002-2014        |
| MSL – Moisture Sensitivity Level | Level 3   | IPC/JEDEC J-STD-020      |



Caution!  
ESD-Sensitive Device

## Solderability

Compatible with both lead-free (260°C max. reflow temp.) and tin/lead (245°C max. reflow temp.) soldering processes. The use of no-clean solder to avoid washing after soldering is highly recommended.

Contact plating: Ni-Au

## RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- PFOS Free

## Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

**Web:** [www.qorvo.com](http://www.qorvo.com)

**Tel:** 1-844-890-8163

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## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,  
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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